ABSOLUTE MAXIMUM RATINGS

These are stress ratings only and functional operation of the device at these or any other above those indicated in the operation sections of the specifications below is not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect reliability.

V _{CC}	+6V (V _{cc} – 0.3V) to +13.2V
	13.2V
Input Voltages	
T _{IN}	$-0.3V$ to $(V_{CC} + 0.3V)$
R	±20V
Output Voltages	
Тоит	$(V^+, +0.3V)$ to $(V^-, -0.3V)$
R _{0.17}	$-0.3V$ to $(V_{cc} + 0.3V)$
Short Circuit Duration or	. (V ⁺ , +0.3V) to (V ⁻ , -0.3V)0.3V to (V $_{\rm CC}$ +0.3V) n $T_{\rm OUT}$ Continuous

Power Dissipation Per Package

24-pin SSOP (derate 11.2mW/°C above +70°C)...900mW 24-pin SOIC (derate 12.5mW/°C above +70°C)...1000mW 28-pin SSOP (derate 11.2mW/°C above +70°C)...900mW 28-pin SOIC (derate 12.7mW/°C above +70°C)...1000mW

SPECIFICATIONS

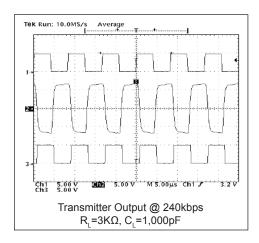
 V_{cc} at nominal ratings; $0.1\mu F$ charge pump capacitors; T_{MIN} to T_{MAX} , unless otherwise noted.

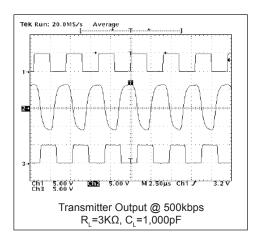
PARAMETER	MIN.	TYP.	MAX.	UNIT	CONDITIONS
TTL INPUTS					T _{IN} , EN, SD
Logic Threshold V _{IL}			0.8	Volts	
Logic Threshold V _{IH}	2.0			Volts	
Logic Pull-Up Current		15	200	μΑ	T _{IN} = 0V
Maximum Transmission Rate	480			kbps	$C_{L} = 1000 pF, R_{L} = 3k\Omega$
TTL OUTPUTS					•
Compatibility		TTL/CMO	S		
V _{OL}			0.4	Volts	I _{OUT} = 3.2mA: Vcc = +5V
V _{OH}	3.5			Volts	I _{OUT} = -1.0mA
Leakage Current		0.05	+/-10	μA	$0V \le V_{OUT} \le VCC$; SP211EH \overline{EN} = 0V; SP213EH EN = VCC, $T_A = +25^{\circ}C$
RS-232 OUTPUT					
Output Voltage Swing	+/-5	+/-7		Volts	All transmitter outputs loaded with 3kΩ to ground
Output Resistance	300			Ω	Vcc = 0V; V _{OUT} = +/-2V
Output Short Circuit Current		+/-25		mA	Infinite Duration, V _{OUT} = 0V
RS-232 INPUT		^			
Voltage Range	-15		+15	Volts	
Voltage Threshold Low	0.8	1.2		Volts	Vcc = 5V, T _A = +25°C
Voltage Threshold High		1.7	2.8	Volts	Vcc = 5V, T _A = +25°C
Hysteresis	0.2	0.5	1.0	Volts	Vcc = 5V
Resistance	3	5	7	kΩ	$V_{IN} = +/-15V, T_{A} = +25^{\circ}C$
DYNAMIC CHARACTERISTICS	3				
Driver Propagation Delay		250		ns	TTL to RS-232
Receiver Propagation Delay		200	500	ns	RS-232 to TTL
Instantaneous Slew Rate			TBD	V/µs	$C_L = 2500 \text{pF}, R_L = 3 \text{k}\Omega;$ $T_A = +25^{\circ}\text{C}; \text{ from +/-3V}$

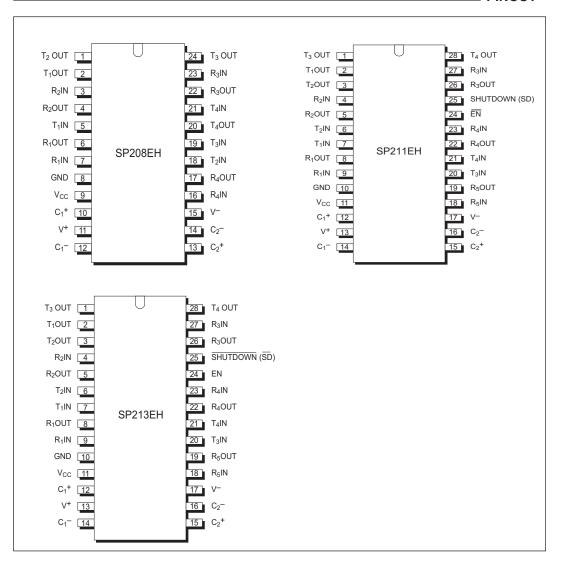
SPECIFICATIONS

 $V_{_{CC}} \ at \ nominal \ ratings; \ 0.1 \mu F \ charge \ pump \ capacitors; \ T_{_{MIN}} \ to \ T_{_{MAX'}} \ unless \ otherwise \ noted.$

PARAMETER	MIN.	TYP.	MAX.	UNIT	CONDITIONS
DYNAMIC CHARACTERISTICS continued					
Transition Time			TBD	μs	C_L = 2500pF, R_L = 3k Ω , Measured from -3V to +3V or +3V to -3V
Output Enable Time		400		ns	
Output Disable Time		250		ns	
POWER REQUIREMENTS					
Vcc	4.50	5.00	5.50	Volts	
Icc		3	6	mA	No Load: Vcc = +/-10%
Icc		15		mA	All Transmitters $R_L = 3k\Omega$
Shutdown Current		1	10	μA	T _A = +25°C
ENVIRONMENTAL AND MECHA	NICAL				
Operating Temperature					
Commercial, _C	0		+70	°C	
Extended, _E	-40		+85	°C	
Storage Temperature	-65		+125	°C	
Package _A _T			OP) small IC) small c		







FEATURES

As in the original RS-232 multi-channel products, the **SP208EH**, **SP211EH** and **SP213EH** high speed multi-channel RS-232 line transceivers provide a variety of configurations to fit most designs, especially high speed applications where +/-12V is not available. The **SP208EH/211EH/213EH** is a superior high speed drop-in replacement to our previous versions as well as popular industry standards.

All devices in this series feature low–power CMOS construction and **Exar's**–proprietary on-board charge pump circuitry to generate the RS-232 signal voltages. The ability to use 0.1µF charge pump capacitors saves board space and reduces production costs. The devices in this series provide different driver/receiver combinations to match any application requirement.

The **SP211EH** and **SP213EH** models feature a low–power shutdown mode, which reduces power supply drain to 1µA. The **SP213EH** includes a Wake-Up function which keeps two receivers active in the shutdown mode, unless disabled by the EN pin.

The family is available in 28 and 24 pin SO (wide) and SSOP (shrink) small outline packages. Devices can be specified for commercial (0°C to +70°C) and industrial/extended (-40°C to +85°C) operating temperatures.

THEORY OF OPERATION

The SP208EH, SP211EH and SP213EH devices are made up of three basic circuit blocks — 1) transmitter/driver, 2) receiver and 3) the EXAR—proprietary charge pump. Each model within the series incorporates variations of these circuits to achieve the desired configuration and performance.

Transmitter/Drivers

The drivers of this series can maintain a typical data rate of 500kbps.

This superior RS-232 data transmission rate makes the **SP208EH/211EH/213EH** series an ideal match for many designs in personal computer peripherals and LAN applications that demand high speed performance.

The drivers are inverting transmitters, which accept either TTL or CMOS inputs and output the RS-232 signals with an inverted sense relative to the input logic levels. Typically, the RS-232 output voltage swing is +/-9V with no load, and +/-5V minimum with full load. The transmitter outputs are protected against infinite short—circuits to ground without degradation in reliability. The drivers of the **SP211EH**, and **SP213EH** can be tri—stated by using the SHUTDOWN function.

In the "power-off" state, the output impedance will remain greater than 300 ohms, again satisfying the RS-232 specifications. Should the input of the driver be left open, an internal 400k ohm pull-up resistor to Vcc forces the input high, thus committing the output to a low state. The slew rate of the transmitter output is internally limited to a maximum of 30V/µs in order to meet the EIA/RS-232 and ITU V.28 standards. The transition of the output from high to low also meets the monotonicity requirements of the standard.

Receivers

The high performance receivers of the SP208EH/211EH/213EH devices can accept input signals at a typical data rate or 500kbps. The receivers convert RS-232 level input signals to inverted TTL level signals. Since the input is usually from a transmission line where long cable lengths and system interference can degrade the signal, the inputs have a typical hysteresis margin of 500mV. This ensures that the receiver is virtually immune to noisy transmission lines. Should an input be left unconnected, a $5\mathrm{k}\Omega$ pull-down resistor to ground will commit the output of the receiver to a high state.

SHUTDOWN MODE

The **SP211EH** and **SP213EH** both feature a control input which will disable the device and reduce power supply to less than $10\mu A$, making the parts ideal for battery-powered systems. In the "shutdown" mode the receivers and transmitters will both be tristated. The V+ output of the charge pump will discharge to Vcc and the V- output will discharge to ground.

For complete shutdown to occur and the 10µA power drain to be realized, the following conditions must be met:

SP211EH:

- +5V must be applied to the SD pin.
- ENABLE must be either 0V, +5V or not connected
- the transmitter inputs must be either
 +5.0V or not connected
- Vcc must be +5V
- Receiver inputs must be >0V and <+5V

SP213EH:

- 0V must be applied top the SD pin
- ENABLE must be either 0V, +5.0V or not connected
- the transmitter inputs must be either +5.0V or not connected
- Vcc must be +5V
- Receiver inputs must be >0V and <+5V

ENABLE

SP211EH and SP213EH feature an enable input, which allows the receiver outputs to be either tri–stated or enabled. This can be especially useful when the receiver is tied directly to a shared microprocessor data bus. For the SP211EH, enable is active low; that is, 0V applied to the ENABLE pin will enable the receiver outputs. For the SP213EH, enable is active high; that is, +5V applied to the ENABLE pin will enable the receiver outputs.

WAKE-UP FUNCTION

The **SP213EH** has a wake-up feature that keeps two receivers (R4 and R5) in an enabled state when the device is in shutdown mode. With only the receivers active during shutdown, the devices draw 5-10µA of supply current.

Atypical application of this function would be where a modem is interfaced to a computer in a power-down mode. The ring indicator signal from the modem could be passed through an active receiver in the SP213EH that is itself in the shutdown mode. The ring indicator signal would propagate through the SP213EH to the power management circuitry of the computer to power up the microprocessor and the SP213EH drivers. After the supply voltage to the SP213EH reaches +5.0V, the SHUTDOWN pin can be disabled, taking the SP213EH out of the shutdown mode.

All receivers that are active during shutdown maintain 500mV (typical) of hysteresis.

SD	EN	Power Up/Down	Receiver Outputs
1	1	Up	Enable
1	0	Up	Tri-state
0	1	Down	Enable
0	0	Down	Tri-State

Table 2. SP213EH Wake-Up Truth Table

SD	ΕN	Power Up/Down	Receiver Outputs
0	0	Up	Enable
0	1	Up	Tri-state
1	0	Down	Enable
1	1	Down	Tri-State

Table 3. SP211EH Receiver Truth Table

6

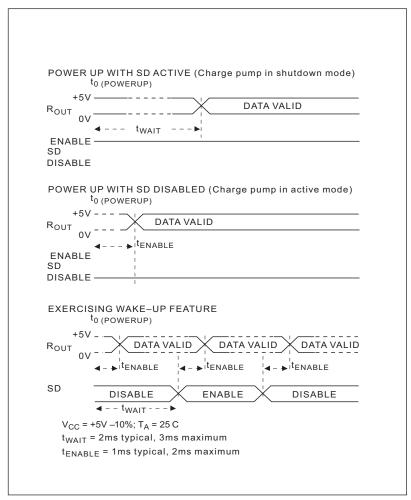


Figure 6. Wake-Up Timing

Charge-Pump

The charge pump is a **Exar**-patented design (5,306,954) and uses a unique approach compared to older less-efficient designs. The charge pumps still requires four external capacitors, but uses a four-phase voltage shifting technique to attain symmetrical 10V power supplies. Figure 3a shows the waveform found on the positive side of capacitor C2, and Figure 3b shows the negative side of capacitor C2. There is a free-running oscillator that controls the four phases of the voltage shifting. A description of each phase is as follows:

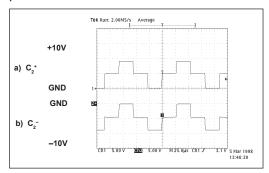


Figure 5. Typical waveforms seen on capacitor C2 when all drivers are at maximum load.

Phase 1

 $-V_{SS}$ charge storage -During this phase of the clock cycle, the positive side of capacitors C_1 and C_2 are initially charged to +5V. C_1^+ is then switched to ground and charge on C_1^- is transferred to C_2^- . Since C_2^+ is connected to +5V, the voltage potential across capacitor C_2^- is now 10V.

Phase 2

 $-V_{ss}$ transfer — Phase two of the clock connects the negative terminal of C_2 to the V_{ss} storage capacitor and the positive terminal of C_2 to ground, and transfers the generated -10V to C_3 . Simultaneously, the positive side of capacitor C_1 is switched to +5V and the negative side is connected to ground.

Phase 3

V_{DD} charge storage — The third phase of the clock is identical to the first phase
 the charge transferred in C₁ produces

-5V in the negative terminal of C_1 , which is applied to the negative side of capacitor C_2 . Since C_2^+ is at +5V, the voltage potential across C_2 is 10V.

Phase 4

- $\rm V_{DD}$ transfer - The fourth phase of the clock connects the negative terminal of $\rm C_2$ to ground and transfers the generated IOV across $\rm C_2$ to $\rm C_4$, the $\rm V_{DD}$ storage capacitor. Again, simultaneously with this, the positive side of capacitor $\rm C_1$ is switched to +5V and the negative side is connected to ground, and the cycle begins again.

Since both V+ and V⁻ are separately generated from $V_{\rm CC}$ in a no–load condition, V+ and V⁻ will be symmetrical. Older charge pump approaches that generate V⁻ from V+ will show a decrease in the magnitude of V⁻ compared to V+ due to the inherent inefficiencies in the design.

The clock rate for the charge pump typically operates at 15kHz. The external capacitors must be a minimum of $0.1\mu F$ with a 16V breakdown rating.

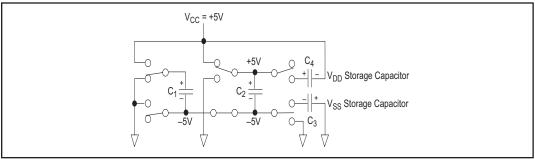


Figure 6, Charge Pump - Phase 1

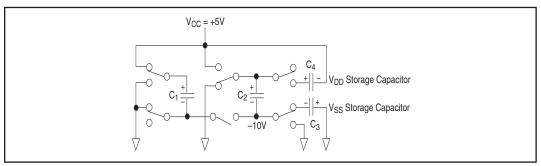


Figure 7, Charge Pump - Phase 2

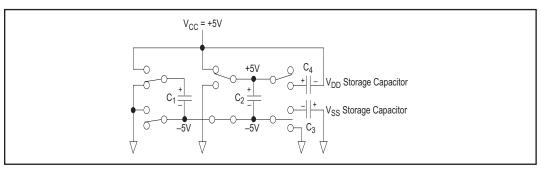


Figure 8, Charge Pump - Phase 3

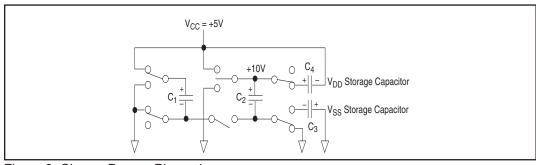


Figure 9, Charge Pump - Phase 4

ESD TOLERANCE

The SP208EH/211EH/213EH family incorporates ruggedized ESD cells on all driver output and receiver input pins. The ESD structure is improved over our previous family for more rugged applications and environments sensitive to electro-static discharges and associated transients. The improved ESD tolerance is at least ±15kV without damage nor latch-up.

There are different methods of ESD testing applied:

- a) MIL-STD-883, Method 3015.7
- b) IEC61000-4-2 Air-Discharge
- c) IEC61000-4-2 Direct Contact

The Human Body Model has been the generally accepted ESD testing method for semiconductors. This method is also specified in MIL-STD-883, Method 3015.7 for ESD testing. The premise of this ESD test is to simulate the human body's potential to store electro-static energy and discharge it to an integrated circuit. The simulation is performed by using a test model as shown in Figure 10. This method will test the IC's capability to withstand an ESD transient during normal handling such as in manufacturing areas where the IC's tend to be handled frequently.

The IEC-61000-4-2, formerly IEC801-2, is generally used for testing ESD on equipment

and systems. For system manufacturers, they must guarantee a certain amount of ESD protection since the system itself is exposed to the outside environment and human presence. The premise with IEC61000-4-2 is that the system is required to withstand an amount of static electricity when ESD is applied to points and surfaces of the equipment that are accessible to personnel during normal usage. The transceiver IC receives most of the ESD current when the ESD source is applied to the connector pins. The test circuit for IEC61000-4-2 is shown on Figure 11. There are two methods within IEC61000-4-2, the Air Discharge method and the Contact Discharge method.

With the Air Discharge Method, an ESD voltage is applied to the equipment under test (EUT) through air. This simulates an electrically charged person ready to connect a cable onto the rear of the system only to find an unpleasant zap just before the person touches the back panel. The high energy potential on the person discharges through an arcing path to the rear panel of the system before he or she even touches the system. This energy, whether discharged directly or through air, is predominantly a function of the discharge current rather than the discharge voltage. Variables with an air discharge such as approach speed of the object carrying the ESD potential to the system and humidity will tend to change the discharge current. For example, the rise time of the discharge current varies with the approach speed.

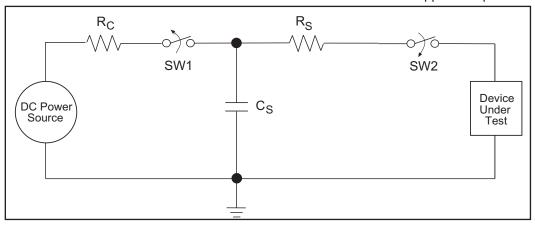


Figure 10. ESD Test Circuit for Human Body Model

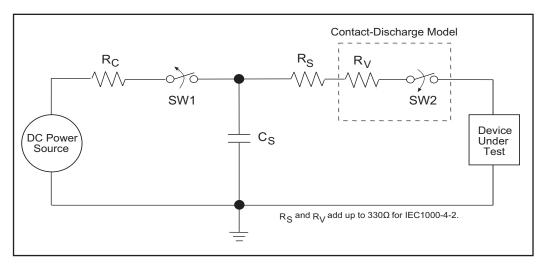


Figure 11. ESD Test Circuit for IEC61000-4-2

The Contact Discharge Method applies the ESD current directly to the EUT. This method was devised to reduce the unpredictability of the ESD arc. The discharge current rise time is constant since the energy is directly transferred without the air-gap arc. In situations such as hand held systems, the ESD charge can be directly discharged to the equipment from a person already holding the equipment. The current is transferred on to the keypad or the serial port of the equipment directly and then travels through the PCB and finally to the IC.

The circuit model in Figures 10 and 11 represent the typical ESD testing circuit used for all three methods. The $C_{\rm S}$ is initially charged with the DC power supply when the first switch (SW1) is on. Now that the capacitor is charged, the second switch (SW2) is on while SW1 switches off. The voltage stored in the capacitor is then applied through $R_{\rm S}$, the current limiting resistor, onto the device under test (DUT). In ESD tests, the SW2 switch is pulsed so that the device under test receives a duration of voltage.

For the Human Body Model, the current limiting resistor ($R_{\rm S}$) and the source capacitor

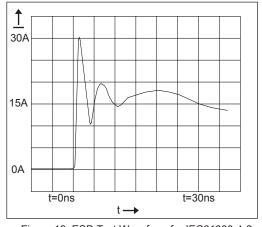


Figure 12. ESD Test Waveform for IEC61000-4-2

 (C_{S}) are 1.5k Ω an 100pF, respectively. For IEC-61000-4-2, the current limiting resistor (R_{S}) and the source capacitor (C_{S}) are 330 Ω an 150pF, respectively.

The higher C_s value and lower R_s value in the IEC61000-4-2 model are more stringent than the Human Body Model. The larger storage capacitor injects a higher voltage to the test point when SW2 is switched on. The lower current limiting resistor increases the current charge onto the test point.

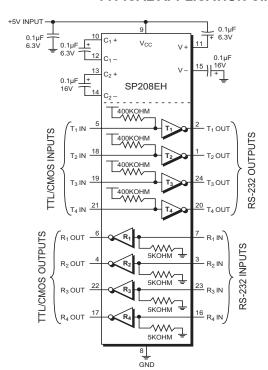
EIA STANDARDS

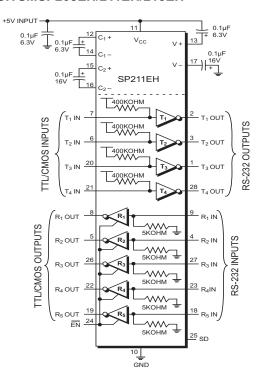
The Electronic Industry Association (EIA) developed several standards of data transmission which are revised and updated in order to meet the requirements of the industry. In data processing, there are two basic means of communicating between systems and components. The RS--232 standard was first introduced in 1962 and, since that time, has become an industry standard. The RS-232 is a relatively slow data exchange protocol, with a maximum baud rate of only 20kbps, which can be transmitted over a maximum copper wire cable length of 50 feet. The SP208EH/211EH/213EH series of data communications interface products have been designed to meet both the EIA protocol standards, and the needs of the industry.

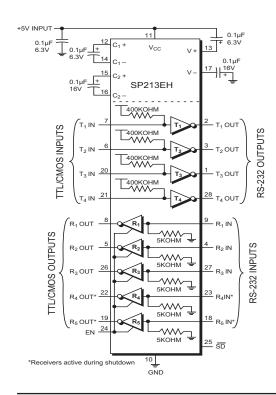
DEVICE PIN TESTED	HUMAN BODY MODEL	Air Discharge	IEC16000-4-2 Direct Contact	Level
Driver Outputs	±15kV	<u>+</u> 15kV	<u>+</u> 8kV	4
Receiver Inputs	±15kV	<u>+</u> 15kV	<u>+</u> 8kV	4

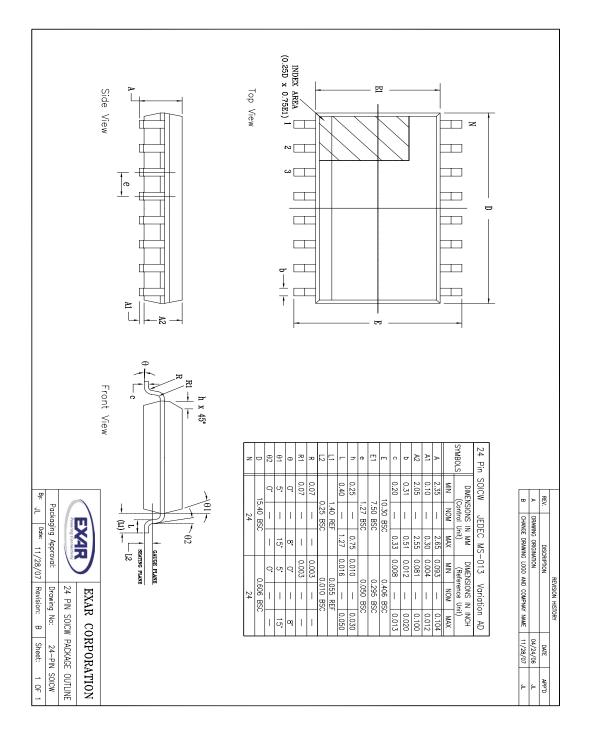
Table 3. Transceiver ESD Tolerance Levels

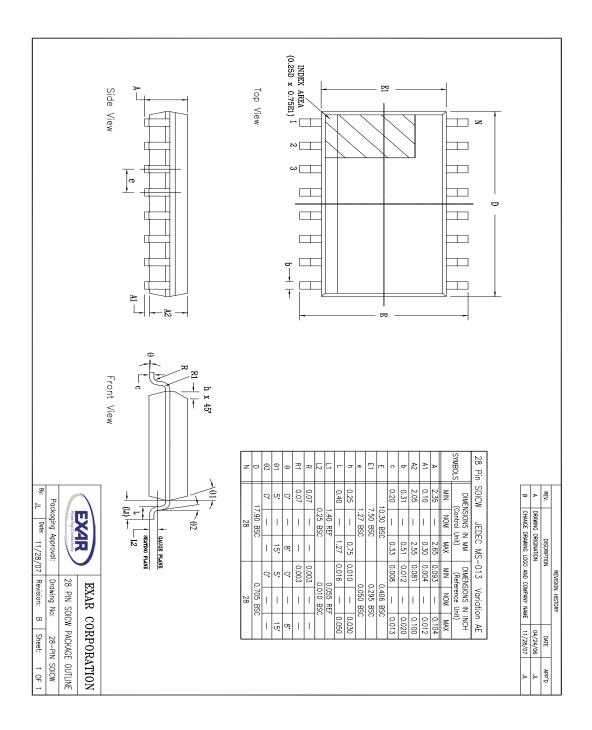
TYPICAL APPLICATION CIRCUITS...SP208EH/211EH/213EH

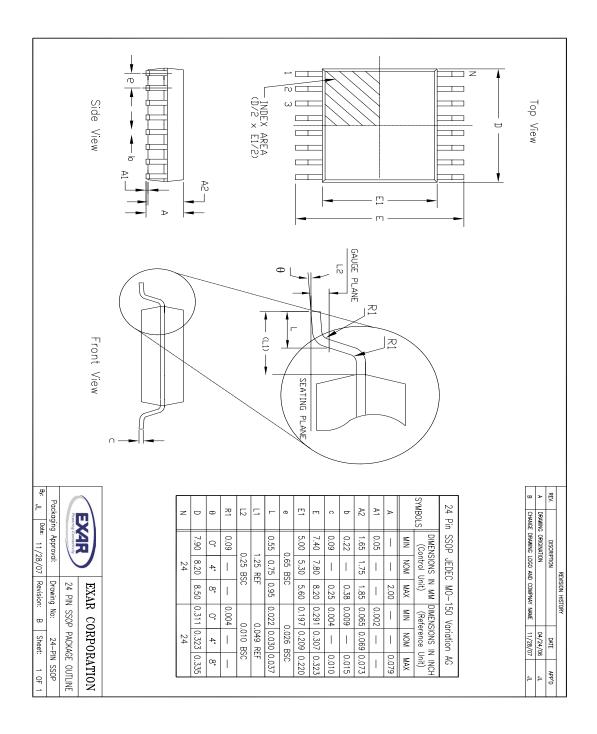


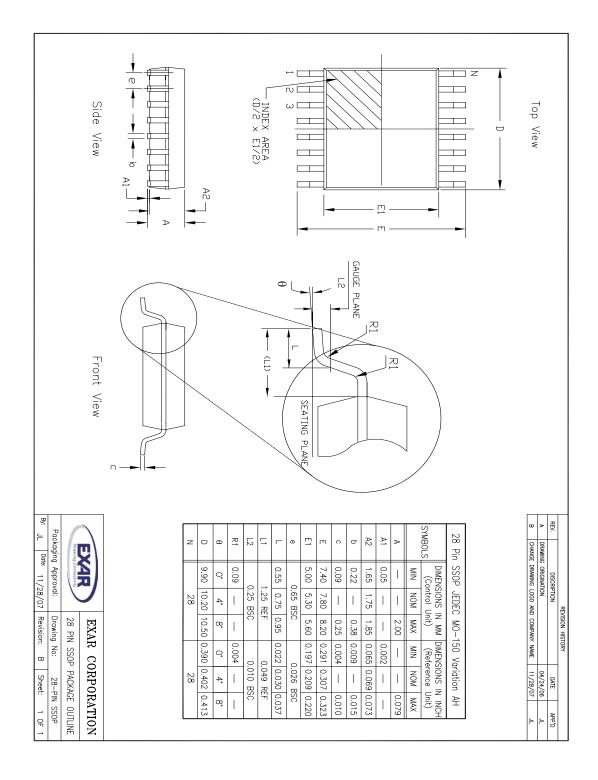












ORDERING INFORMATION				
RS232 Transceivers:				
Model Drivers	Receivers	Temperature Range	Package Type	
SP208EHCA-L4	4	0°C to +70°C	24-pin SSOF	
SP208EHCT-L44	4	0°C to +70°C	24-pin SOIC	
SP208EHEA-L4	4	40°C to +85°C	24-pin SSOF	
SP208EHET-L44	4	40°C to +85°C	24-pin SOIC	
SP211EHCT-L44				
SP211EHEA-L44	5	-40°C to +85°C40°C to +85°C	28–pin SSOF	
SP211EHEA-L44	55		28-pin SSOF 28-pin SOIC	
P211EHEA-L4	5		28-pin SSOI28-pin SOIC Ction:28-pin SOIC	
P211EHEA-L	ow–Power Shutdown, Tri Receivers	—40°C to +85°C—40°C to +85°C— —state Enable, and Wake—Up Fun —temperature Range	28-pin SSOI28-pin SOI Ction:Package Type28-pin SSOI	
P211EHEA-L	5			

Please consult the factory for pricing and availability on a Tape-On-Reel option.

DATE	REVISION	DESCRIPTION
08		Legacy Sipex Datasheet
10/28/10	1.0.0	Convert to Exar format, update ordering information and change rev to 1.0.0

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